

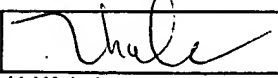
First Named Inventor	Leonard Forbes	<b>INFORMATION DISCLOSURE STATEMENT FORM PTO-1449</b>
Serial No.	10/714,753	
Filing Date	November 17, 2003	
Group Art Unit	2818	
Examiner Name	Unknown	
Confirmation No.	3377	
Attorney Docket No.	400.260US01	
Title: NROM FLASH MEMORY DEVICES ON ULTRATHIN SILICON		Sheet 1 of 7

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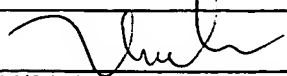
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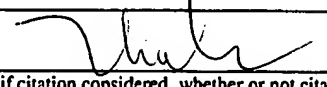
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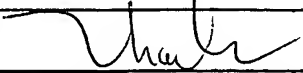
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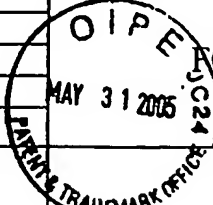
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